74AHC123A; 74AHCT123A

Dual retriggerable monostable multivibrator with reset Rev. 4 — 8 November 2011 Product da

Product data sheet

General description 1.

The 74AHC123A; 74AHCT123A are high-speed Si-gate CMOS devices and are pin compatible with Low power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard no. 7A.

The 74AHC123A; 74AHCT123A are dual retriggerable monostable multivibrators with output pulse width control by three methods. The basic pulse time is programmed by selection of an external resistor (R_{FXT}) and capacitor (C_{FXT}). The external resistor and capacitor are normally connected as shown in Figure 11.

Once triggered, the basic output pulse width may be extended by retriggering the gated active LOW-going edge input (nA) or the active HIGH-going edge input (nB). By repeating this process, the output pulse period (nQ = HIGH, nQ = LOW) can be made as long as desired. Alternatively an output delay can be terminated at any time by a LOW-going edge on input nRD, which also inhibits the triggering.

An internal connection from nRD to the input gate makes it possible to trigger the circuit by a positive-going signal at input nRD as shown in Table 3. Figure 8 and Figure 9 illustrate pulse control by retriggering and early reset. The basic output pulse width is essentially determined by the value of the external timing components R_{FXT} and C_{FXT}. When $C_{EXT} \ge 10$ nF, the typical output pulse width is defined as: $t_W = R_{EXT} \times C_{EXT}$ where t_W = pulse width in ns; R_{FXT} = external resistor in $k\Omega$; C_{FXT} = external capacitor in pF. Schmitt-trigger action at all inputs makes the circuit highly tolerant to slower input rise and fall times.

Features and benefits 2.

- All inputs have a Schmitt-trigger action
- Inputs accept voltages higher than V_{CC}
- DC triggered from active HIGH or active LOW inputs
- Retriggerable for very long pulses up to 100 % duty factor
- Direct reset terminates output pulse
- For 74AHC123A only: operates with CMOS input levels
- For 74AHCT123A only: operates with TTL input levels
- ESD protection:
 - HBM JESD22-A114E exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

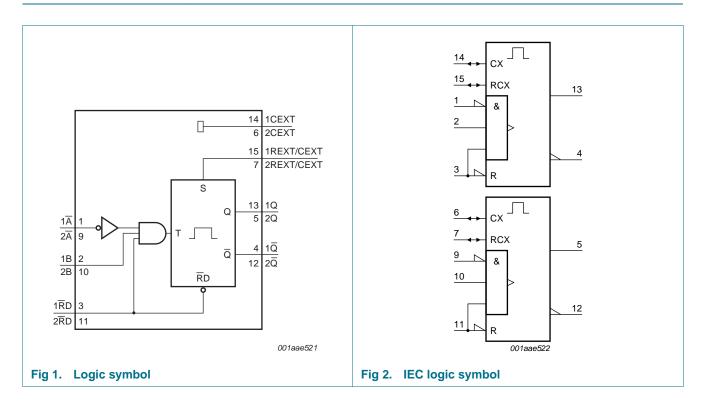


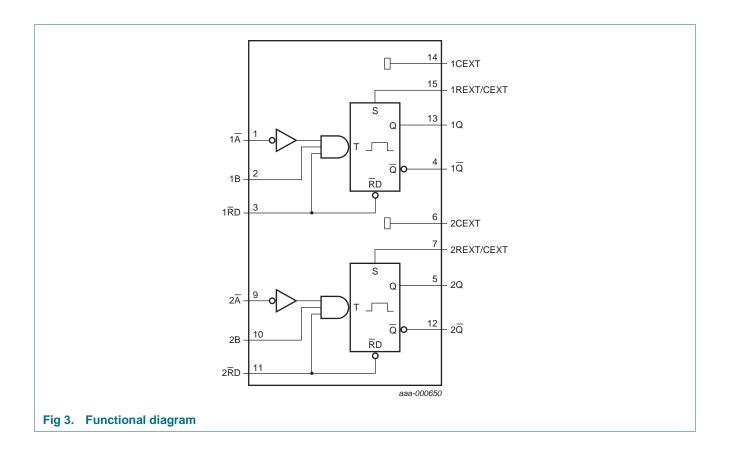
3. Ordering information

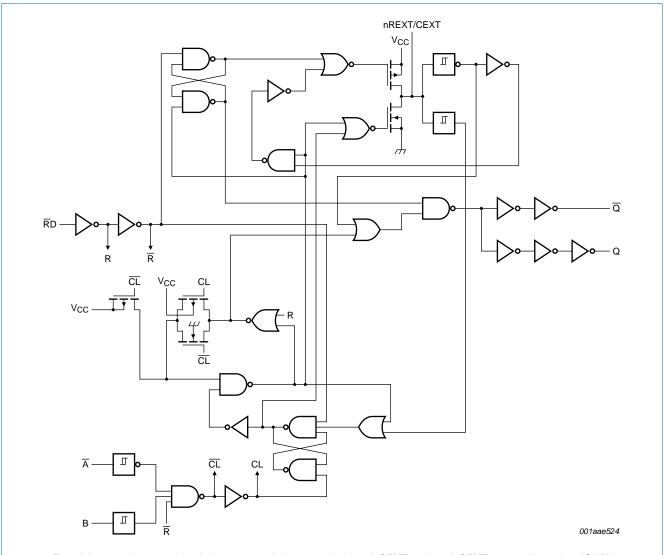
Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC123AD	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads;	SOT109-1
74AHCT123AD			body width 3.9 mm	
74AHC123APW	N -40 °C to +125 °C TSSOP16 plastic thin shrink sn		,	SOT403-1
74AHCT123APW			body width 4.4 mm	
74AHC123ABQ	–40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced	SOT763-1
74AHCT123ABQ			very thin quad flat package; no leads; 16 terminals; body $2.5 \times 3.5 \times 0.85$ mm	

4. Functional diagram





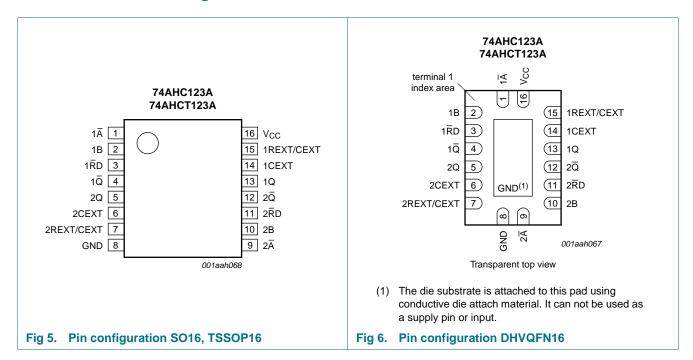


For minimum noise generation it is recommended to ground pins 6 (2CEXT) and 14 (1CEXT) externally to pin 8 (GND).

Fig 4. Functional diagram

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description	
1Ā	1	negative-edge triggered input 1	
1B	2	positive-edge triggered input 1	
1RD	3	direct reset LOW and positive-edge triggered input 1	
1Q	4	active LOW output 1	
2Q	5	active HIGH output 2	
2CEXT	6	external capacitor connection 2	
2REXT/CEXT	7	external resistor and capacitor connection 2	
GND	8	ground (0 V)	
2 A	9	negative-edge triggered input 2	
2B	10	positive-edge triggered input 2	
2RD	11	direct reset LOW and positive-edge triggered input 2	
2Q	12	active LOW output 2	
1Q	13	active HIGH output 1	
1CEXT	14	external capacitor connection 1	
1REXT/CEXT	15	external resistor and capacitor connection 1	
V _{CC}	16	supply voltage	

6. Functional description

Table 3. Function table[1]

Input			Output	
nRD	nΑ	nB	nQ	nQ
L	X	X	L	Н
X	Н	Χ	[2]	H[2]
X	Χ	L	[2]	H[2]
Н	L	\uparrow	Л	T
Н	\	Н	Л	T
\uparrow	L	Н	Л	IJ

^[1] H = HIGH voltage level;

L = LOW voltage level;

= one HIGH level output pulse;

= one LOW level output pulse.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_1 < -0.5 V$	<u>[1]</u> –20	-	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> -	±20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	-	±25	mA
I _{CC}	supply current		-	75	mA
I _{GND}	ground current		-75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$			
	SO16 package		[2] _	500	mW
	TSSOP16 package		[3] _	500	mW
	DHVQFN16 package		[4] _	500	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

74AHC_AHCT123A

X = don't care;

^{↑ =} LOW-to-HIGH transition;

 $[\]downarrow$ = HIGH-to-LOW transition;

^[2] If the monostable multivibrator was triggered before this condition was established, the pulse will continue as programmed.

^[2] Ptot derates linearly with 8 mW/K above 70 °C.

^[3] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

^[4] Ptot derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC	123A		74AHC	Г123А		V V V °C ns/V
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V_{I}	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise	V_{CC} = 3.3 V \pm 0.3 V	-	-	100	-	-	-	ns/V
a	and fall rate	$V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	-	-	20	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C	3	-40 °C t	to +85 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74AHC1	23A			1				ı	1	
V _{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V_{IL}	LOW-level	$V_{CC} = 2.0 \text{ V}$	-	-	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
	HICH lovel	V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V_{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = -50 \mu A$; $V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
	voltage	$I_{O} = -50 \mu A; V_{CC} = 3.0 V$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \mu A$; $V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 50 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
	voitage	$I_O = 50 \mu A; V_{CC} = 3.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_O = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
l _l	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$								
		nREXT/CEXT	[1] -	-	±0.25	-	±2.5	-	±10.0	μΑ
		pins n \overline{A} , nB, n $\overline{R}D$	-	-	±0.1	-	±1.0	-	±2.0	μΑ

Table 6. Static characteristics ...continued Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions			25 °C	;	-40 °C t	:o +85 °C	-40 °C t	o +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
Icc	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V		-	-	4.0	-	40	-	80	μА
		active state (per circuit); V _I = V _{CC} or GND	[1]								
		$V_{CC} = 3.0 \text{ V}$		-	160	250	-	280	-	280	μΑ
		V _{CC} = 4.5 V		-	380	500	-	650	-	650	μΑ
		$V_{CC} = 5.5 \text{ V}$		-	560	750	-	975	-	975	μΑ
Cı	input capacitance			-	5.0	10	-	10	-	10	pF
Co	output capacitance			-	4.0	-	-	-	-	-	pF
74AHCT	123A										
V _{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		2.0	-	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		-	-	8.0	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$									
	output voltage	$I_{O} = -50 \ \mu A$		4.4	4.5	-	4.4	-	4.4	-	V
voitage	voitage	$I_{O} = -8.0 \text{ mA}$		3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$									
	output voltage	$I_O = 50 \mu A$		-	0	0.1	-	0.1	-	0.1	V
	voitage	$I_0 = 8.0 \text{ mA}$		-	-	0.36	-	0.44	-	0.55	V
l _l	input leakage current	nREXT/CEXT; $V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	[1]	-	-	±0.25	-	±2.5	-	±10.0	μА
		pins $n\overline{A}$, nB , $n\overline{R}D$; $V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$		-	-	±0.1	-	±1.0	-	±2.0	μА
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V		-	-	4.0	-	40	-	80	μΑ
		active state (per circuit); V _I = V _{CC} or GND	[1]								
		V _{CC} = 4.5 V		-	380	500	-	650	-	650	μΑ
		V _{CC} = 5.5 V		-	560	750	-	975	-	975	μΑ
Cı	input capacitance			-	3	10	-	10	-	10	pF
Co	output capacitance			-	4.0	-	-	-	-	-	pF

^[1] Voltage on nREXT/CEXT = $0.5 \times V_{CC}$ and pin nREXT/CEXT in OFF-state during test.

10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; For test circuit see Figure 12.

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	-40 °C t	o +125 °C	Unit
				Min	Typ[1]	Max	Min	Max	Min	Max	
74AHC1	23A				•		'	'	'	'	
t _{pd}	propagation delay	$n\overline{A}$ and nB to nQ and $n\overline{Q}$; see Figure 7	[2]								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		$C_L = 15 pF$		-	7.4	20.6	1.0	24.0	1.0	26.0	ns
		$C_L = 50 pF$		-	10.5	24.1	1.0	27.5	1.0	30.0	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		$C_L = 15 pF$		-	5.1	12.0	1.0	14.0	1.0	15.5	ns
		$C_L = 50 pF$		-	7.3	14.0	1.0	16.0	1.0	17.5	ns
		\overline{nRD} to \overline{nQ} and \overline{nQ} ; see Figure 7	[2]								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		C _L = 15 pF		-	8.2	22.4	1.0	26.0	1.0	28.0	ns
		$C_L = 50 pF$		-	11.7	25.9	1.0	29.5	1.0	32.0	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		C _L = 15 pF		-	5.6	12.9	1.0	15.0	1.0	16.5	ns
		$C_L = 50 pF$		-	8.1	14.9	1.0	17.0	1.0	19.0	ns
		$\overline{\text{NRD}}$ to $\overline{\text{nQ}}$ and $\overline{\text{nQ}}$ (reset); see Figure 7	[2]								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		C _L = 15 pF		-	6.4	15.8	1.0	18.5	1.0	20.0	ns
		$C_L = 50 pF$		-	9.2	19.3	1.0	22.0	1.0	24.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		C _L = 15 pF		-	4.4	9.4	1.0	11.0	1.0	12.0	ns
		$C_L = 50 pF$		-	6.3	11.4	1.0	13.0	1.0	14.5	ns

Table 7. Dynamic characteristics ...continued GND = 0 V; For test circuit see Figure 12.

Symbol	Parameter	Conditions			25 °C		-40 °C 1	to +85 °C	-40 °C	to +125 °C	Unit
				Min	Typ[1]	Max	Min	Max	Min	Max	
t_{W}	pulse width	inputs; nA = LOW; see <u>Figure 7</u>									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		5.0	-	-	5.0	-	5.0	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		5.0	-	-	5.0	-	5.0	-	ns
		inputs; nB = HIGH; see <u>Figure 7</u>									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		5.0	-	-	5.0	-	5.0	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		5.0	-	-	5.0	-	5.0	-	ns
	se	inputs; $\overline{RD} = LOW$; see Figure 7									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		5.0	-	-	5.0	-	5.0	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		5.0	-	-	5.0	-	5.0	-	ns
		outputs; $n\overline{Q}$ = LOW and nQ = HIGH; C_L = 50 pF; see Figure 7, Figure 8, Figure 9 and Figure 10	[3]								
		$C_{EXT} = 28 \text{ pF}; R_{EXT} = 2 \text{ k}\Omega$									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	115	240	-	300	-	300	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		-	100	200	-	240	-	240	ns
		C_{EXT} = 0.01 μ F; R_{EXT} = 10 $k\Omega$									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		90	100	110	90	110	85	115	μS
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		90	100	110	90	110	85	115	μS
		$C_{EXT} = 0.1 \mu F;$ $R_{EXT} = 10 k\Omega;$									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		0.9	1	1.1	0.9	1.1	0.85	1.15	ms
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.9	1	1.1	0.9	1.1	0.85	1.15	ms
t _{rtrig}	retrigger time	\overline{A} to nB; $C_{EXT} = 100$ pF; $R_{EXT} = 1$ k Ω ; $C_L = 50$ pF; see <u>Figure 8</u> and <u>Figure 10</u>									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	60	-	-	-	-	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		-	39	-	-	-	-	-	ns
		$n\overline{A}$ to nB; $C_{EXT} = 0.01 \ \mu F$; $R_{EXT} = 1 \ k\Omega$; $C_L = 50 \ pF$; see <u>Figure 8</u> and <u>Figure 10</u>									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	1.5	-	-	-	-	-	μS
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		-	1.2	-	-	-	-	-	μS
C_{PD}	power dissipation capacitance	$C_L = 50 \text{ pF}; f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	[4]	-	57	-	-	-	-	-	pF

Table 7. Dynamic characteristics ...continued GND = 0 V; For test circuit see Figure 12.

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	-40 °C 1	to +125 °C	Unit
				Min	Typ[1]	Max	Min	Max	Min	Max	
74AHCT	123A						ı	ı			
t _{pd}	propagation delay	$n\overline{A}$ and nB to nQ and $n\overline{Q}$; see Figure 7	[2]								
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		$C_L = 15 pF$		-	5.0	12.0	1.0	14.0	1.0	15.5	ns
		$C_L = 50 pF$		-	7.1	14.0	1.0	16.0	1.0	17.5	ns
		\overline{NRD} to \overline{NRD} to \overline{NRD} ; see Figure 7	[2]								
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		$C_L = 15 pF$		-	5.2	12.9	1.0	15.0	1.0	16.5	ns
		$C_L = 50 pF$		-	7.5	14.9	1.0	17.0	1.0	18.5	ns
		$\overline{\text{NRD}}$ to $\overline{\text{nQ}}$ and $\overline{\text{nQ}}$ (reset); see Figure 7	[2]								
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		C _L = 15 pF		-	4.7	9.4	1.0	11.0	1.0	12.0	ns
		$C_L = 50 pF$		-	6.7	11.4	1.0	13.0	1.0	14.5	ns
W	pulse width	inputs; $n\overline{A} = LOW$; $C_L = 50 \text{ pF}$; see Figure 7									
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		5.0	-	-	5.0	-	5.0	-	ns
		inputs; nB = HIGH; C _L = 50 pF; see <u>Figure 7</u>									
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		5.0	-	-	5.0	-	5.0	-	ns
		inputs; $\overline{RD} = LOW$; $C_L = 50 \text{ pF}$; see Figure 7									
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		5.0	-	-	5.0	-	5.0	-	ns
		outputs; $n\overline{Q}$ = LOW and nQ = HIGH; C_L = 50 pF; C_{EXT} = 28 pF; R_{EXT} = 2 k Ω ; see <u>Figure 7</u> , <u>Figure 8</u> , <u>Figure 9</u> and <u>Figure 10</u>	[3]								
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		-	100	200	-	240	-	240	ns
		$C_{EXT} = 0.01 \mu F;$ $R_{EXT} = 10 k\Omega$									
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		90	100	110	90	110	85	115	μS
		$C_{EXT} = 0.1 \mu F;$ $R_{EXT} = 10 \text{ k}\Omega$									
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.9	1	1.1	0.9	1.1	0.85	1.15	ms

Table 7. Dynamic characteristics ...continued GND = 0 V; For test circuit see Figure 12.

Symbol	Parameter	Conditions			25 °C		–40 °C 1	to +85 °C	-40 °C t	o +125 °C	ns $\mu s \\ pF \\ k\Omega \\ k\Omega \\ pF$
				Min	Typ[1]	Max	Min	Max	Min	Max	
t _{rtrig}	retrigger time	$\overline{\text{NA}}$ to nB; C_{EXT} = 100 pF; R_{EXT} = 1 k Ω ; C_{L} = 50 pF; see <u>Figure 8</u> and <u>Figure 10</u>									
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		-	60	-	-	-	-	-	ns
		n \overline{A} to nB; C_{EXT} = 0.01 μ F; R_{EXT} = 1 k Ω ; C_L = 50 pF; see <u>Figure 8</u> and <u>Figure 10</u>									
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		-	1.5	-	-	-	-	-	μS
C_{PD}	power dissipation capacitance	$C_L = 50 \text{ pF}$; $f_i = 1 \text{ MHz}$; $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	58	-	-	-	-	-	pF
Externa	components	1									
R _{EXT}	external	V _{CC} = 2.0 V		5	-	-	-	-	-	-	kΩ
	resistance	V _{CC} > 3.0 V		1	-	-	-	-	-	-	$k\Omega$
C_{EXT}	external	V _{CC} = 2.0 V	[5]	-	-	-	-	-	-	-	pF
		V _{CC} > 3.0 V	[5]	-	-	-	-	-	-	-	pF

- [1] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} ; C_{EXT} = 0 pF; R_{EXT} = 5 k Ω .
- [3] For $C_{EXT} \ge$ 10 nF the typical value of the pulse width t_W (μ s) = C_{EXT} (nF) \times R_{EXT} ($k\Omega$).
- [4] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

$$P_D = C_{PD} \times V_{CC}{}^2 \times f_i + \sum (C_L \times V_{CC}{}^2 \times f_o)$$
 where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V.

[5] C_{EXT} has no limits.

11. Waveforms

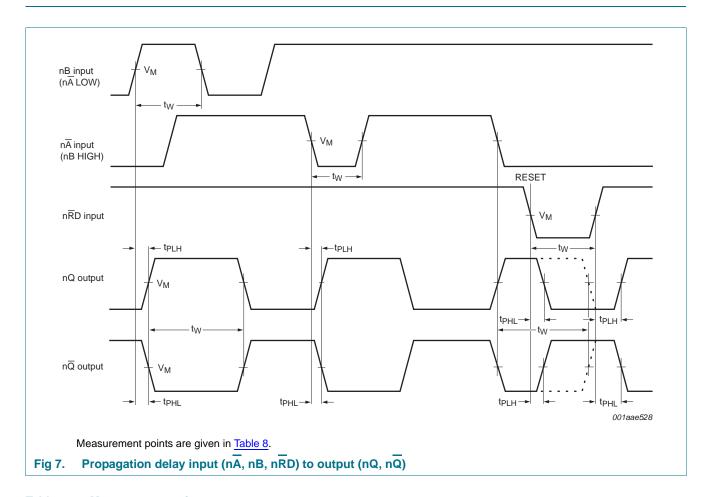
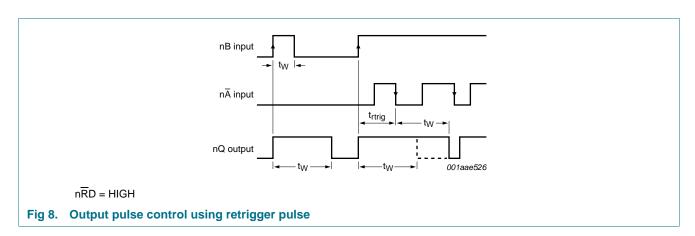
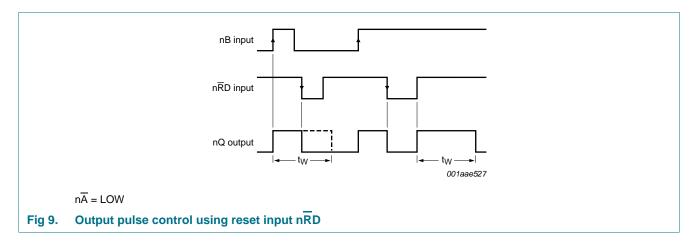


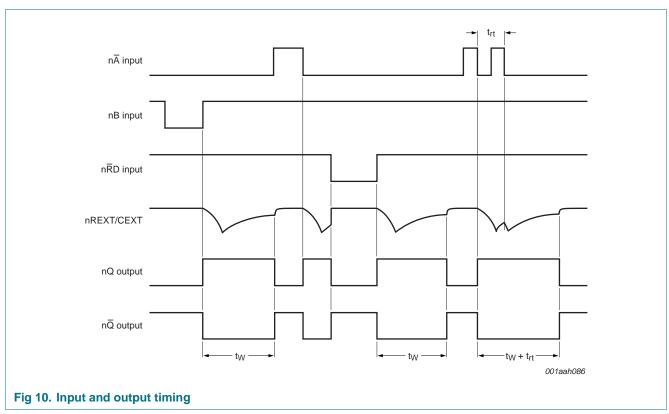
Table 8. Measurement points

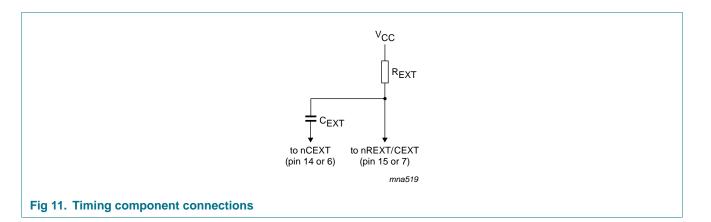
Туре	Input	Output
	V _M	V _M
74AHC123A	0.5V _{CC}	0.5V _{CC}
74AHCT123A	1.5 V	0.5V _{CC}

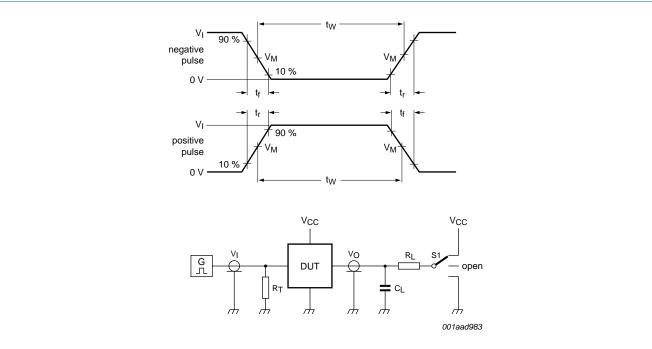


74AHC_AHCT123A









Test data is given in Table 9.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator

 C_L = Load capacitance including jig and probe capacitance

R_L = Load resistor

S1 = Test selection switch

Fig 12. Load circuitry for switching times

Table 9. Test data

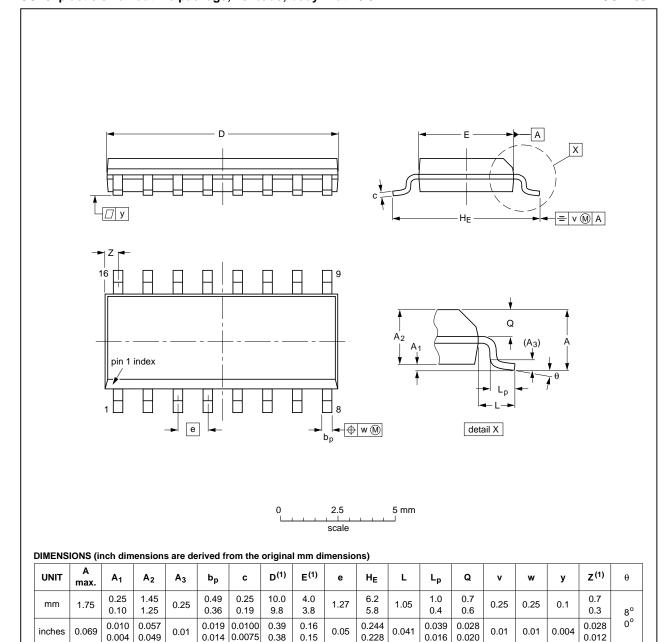
Туре	Input		Load		S1 position			
	VI	t _r , t _f	CL	R _L	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}	
74AHC123A	V_{CC}	3.0 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}	
74AHCT123A	3.0 V	3.0 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}	

74AHC_AHCT123A

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT109-1	076E07	MS-012			99-12-27 03-02-19

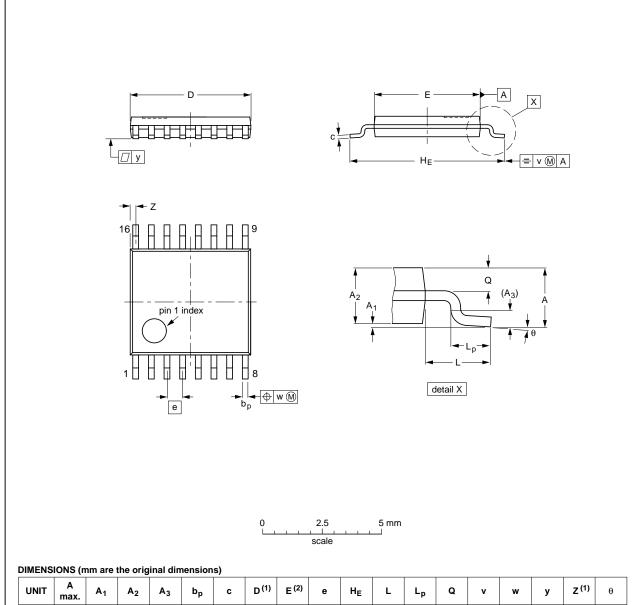
0.15

Fig 13. Package outline SOT109-1 (SO16)

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TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



-							-,												
	UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
	mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE	
SOT403-1		MO-153			99-12-27 03-02-18	
						4

Fig 14. Package outline SOT403-1 (TSSOP16)

74AHC_AHCT123A

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DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm SOT763-1

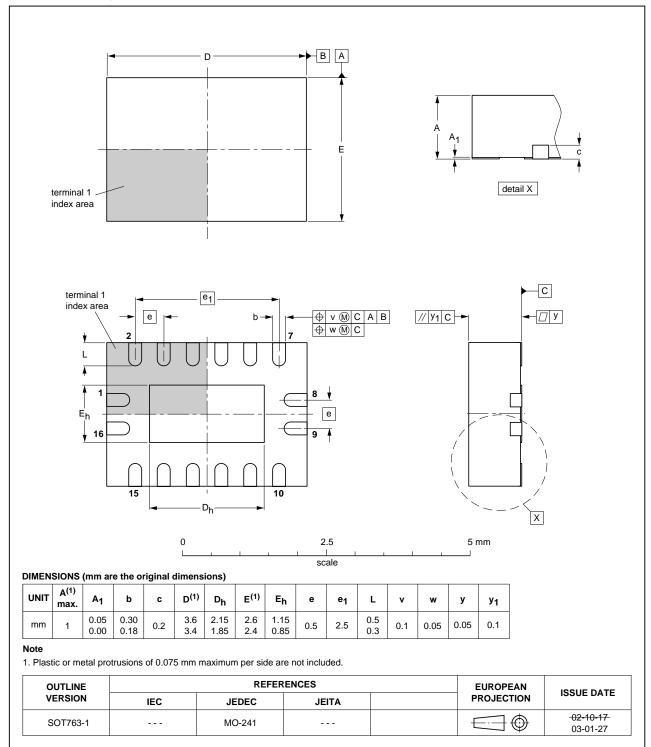


Fig 15. Package outline SOT763-1 (DHVQFN16)

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13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged-Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT123A v.4	20111108	Product data sheet	-	74AHC_AHCT123A v.3
Modifications:	 Legal pages 	updated.		
74AHC_AHCT123A v.3	20110908	Product data sheet	-	74AHC_AHCT123A v.2
74AHC_AHCT123A v.2	20080118	Product data sheet	-	74AHC_AHCT123A v.1
74AHC_AHCT123A v.1	20000315	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Dual retriggerable monostable multivibrator with reset

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74AHC123A; 74AHCT123A

Dual retriggerable monostable multivibrator with reset

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